As the consumer and industrial requirements for compact, high power density, electrical power systems grow substantially over the next decade, development of high-power/energy density capacitor technology is a major enabling technology component element. For microsecond to fractional-second electrical energy storage, discharge, filtering and power conditioning, capacitor technology is unequaled in flexibility and adaptability to meet a broad range of requirements in the future (1–21). This review presents the current status of modern capacitor technology, materials of fabrication, manufacturing technologies, and areas of application. In addition, the largest market sector types of capacitors have future requirements that will be driven by the ever increasing electrification of nearly all aspects of the modern world. Discussions in this article concentrate on commercially available capacitor technologies in broad marketplace use. Those who have an interest in advanced research underway in emerging areas of this technology will find this well addressed in the numerous technical research journals broadly available within international technical societies.

Power kW	Voltage kV	$Run$ Time <sup>b</sup>	
(average)	(peak)	s	Application
$<$ 1	< 50	>1000	• Electronic counter- measures
			$\cdot$ LADAR
			• Communications
			$\cdot$ Computers
			· Uninterruptible power supplies (UPS)
$1 - 10$	$<$ 100	>10	$\cdot$ LADAR
			$\cdot$ RADAR
			• Workstation computers
			• Telecommunications
			• Power quality
			$\cdot$ UPS
$10 - 1000$	< 500	>100	• High-power microwaves
			$\cdot$ RADAR
			• Power quality
			• Distributed power systems
>1000	>100	Single-pulse to	• Directed energy weapons
		continuous	• Antimine
			• Power stabilization/quality
			• Power factor control
			• Industrial processing

**Table 1. Trends in Capacitor Applications and Operating Conditions***<sup>a</sup>*

*<sup>a</sup>* Most systems are projected to be divided by voltage/average power/run-time considerations as shown in the table.

*<sup>b</sup>* Run time refers to one operational cycle. For some applications, such as power factor control, systems run continuously for the entire life of the system.

achieved for pulse durations from 0.05  $\mu$ s to over 1000  $\mu$ s at for these advanced units in production volumes are projected voltages from megavolt levels for microseconds to subkilovolt to be comparable to current technology (7,13,14,19). Projected levels up to millisecond durations (3–5,9,10,12,19–21). Volt- energy densities for advanced storage capacitors are illusage levels have been determined by the nature of the load. trated in Fig. 1. Projected power densities for high frequency Developing innovative new capacitor and related insulation systems operating at near ultimate voltage withstands  $(22 \times$  The observed evolutionary advance rate for capacitor techto  $5\times$  today's operational levels), will enable the achievement nology is about a factor of  $2\times$  per decade in any performance of lightweight systems needed in the future (4–21). Repetition factor well away from *nature's limits* (e.g., such as power denrates will move up to multimegahertz, necessitating inte- sity) (2,3,7,19). If evolution were allowed to drive capacitor grated development of capacitor technology with that of low- technology, meeting these requirements would take 80 to 90 loss  $(\leq 1\%)$  switching topologies and voltage multiplication vears. Therefore, R&D underway now will move toward these transformers (1–20). Most future systems are projected to be requirement-driven performance levels within the next dedivided by voltage/average power/run-time considerations, as cade (7,8). On the other hand, the current advance rate in shown in Table 1 (3–7,9,10,19–21). supported R&D for high-energy, pulse-discharge capacitor

on the opposite sides are charged by a voltage source. The resultant electrical energy of this charged system is stored in the polarized insulating medium and the physically separated surface charges on the electrodes. Capacitors permit storing electrical energy over a long charging time and then release it as required over very short (submicroseconds to multimilliseconds) periods under controlled conditions  $(4,18)$ . Such energy discharge operation, as with filtering duty, requires device technology of very high efficiency per unit volume/mass to minimize thermal management constraints on the system designer, as summarized in Table 1 (4,7,14,15). Particular attention must be given to the life and reliability necessitated by the system requirements. The main classes of capacitor applications are illustrated in Table 2 (7,8,11,14,15,18–21).

### **Scalability of Capacitor Technology**

To date capacitors for ac ripple filtering in dc systems, passive energy storage, and power transfer are unequaled in their geometric flexibility, permitting rapid design optimization for man-portable, vehicular, and large mobile or fixed ground installations for voltages from subkilovolts to megavolts, allowing rapid turnaround time and modular field maintenance (7–19). For future users of advanced power sources, the compact systems being driven by ever-increasing electrification of modern systems would be enabled with capacitor energy and power densities two to ten times those available today (1–15,19). This is potentially feasible and should be conjoined with the possibility of developing advanced capacitor technologies that may well yield capacitors whose performance degrades gracefully, hence, no longer a single point of failure within a power conditioning system  $(7,8,13-15)$ . Indeed, even during normal life and under adverse environments, such a technology would always result in graceful and predictable reduction in performance, so that total system operation could be retained at levels of declining cycle-life performance (7,14).

Table 3 projects next-decade or so future performance of capacitors, building upon the state-of-the-art capacitor technology, and also shows selected examples of several classes of advanced capacitors that R&D might turn into future practical, highly compact systems (1–21). These advanced systems all have the potential for elevating the energy (kJ/kg) and Today, high-energy pulsed power conditioning has been power (kW/kg) densities by a factor of two to ten times. Costs  $ac + dc$  filter capacitors are shown in Fig. 2.

technology for high energy capacitor systems is projected at **Description of the Technology** eighteen times per decade. When applied to the other types A capacitor generally consists of conducting plates or foils of capacitors needed in the next generation power systems, separated by thin layers of an insulating medium. The plates



- Low- and high-frequency filtering in  $ac + dc$  systems
- ac resonant-charging power supplies
- Switched-mode power supplies
- Energy discharge
- High-frequency bypass

*<sup>a</sup>* See Ref. (18–21).

Capacitor System	kJ/kg Now/Future	kW/kg (average power) Now/Future	Rep-Rate Hz	Main Issues
Polymer film	0.4/20	5/20 k	$>1000 \text{ k}$	• New polymer films • Impregnants · Foils and conductors $\cdot$ >200 $\degree$ C $\cdot \ge 1$ kJ/unit • Voltage reversal • Pulse duration • Repetition rate
Ceramic	0.01/5	10/10 k	$>1000 \text{ k}$	• Surface mount-solder reflow stability • Ceramic formulations • Electrodes $\cdot$ >300 $^{\circ}$ C $\cdot$ 1 kJ/unit • Voltage scaling
Electrolytic	0.2/2	2/10 k	>10 k	$\cdot$ Fusing • Electrolytes • Separators $\cdot$ >200 $\rm ^{\circ}C$ $\cdot$ 1 kJ/unit $\cdot$ Gassing • Hermetic sealing • Voltage reversal
Mica	0.005/0.05	5/50 k	$>100$ M	• Pulse repetition rate $\cdot$ Electrodes $\cdot$ >400°C $\cdot$ 1 kJ/unit • Voltage scaling/reversal • Materials $\cdot$ Impregnants

**Table 3. Performance of State-of-the-Art and Advanced Capacitor Systems***<sup>a</sup>*

*<sup>a</sup>* Projects near term and future performance of state-of-the-art capacitor technology and shows selected examples of several classes of advanced capacitors that R&D could turn into future practical, highly compact systems.

cade, provided the necessary R&D is set and maintained plies is selecting available high-power density components  $(3,6,7,11,13,15,19-21)$ . For comparison, Table 4 shows a sum- $(7,14,15,18,19-21)$ . Observations over recent years have mary of the performance parameter ranges of current electro- shown that a technically highly demanding area is the appli-

power conditioning systems and switched-mode power sup-

lyte and polymer film capacitors. cation of capacitors for switched-mode power supplies and **Competitive Advantages of Higher** switching regulators, mainly in the areas of dc input and out-<br> **Power Density Capacitor Technology**<br> **Power Density Capacitor Technology**<br> **Power conditioning system** (2,8,11,14). Only w A major factor in designing the next generation of advanced data on compact (at least two to ten times higher power den-<br>power conditioning systems and switched-mode power sup-<br>sity) capacitors, performing at the higher fr



**Figure 1.** The time line of increasing energy density in energy discharge capacitors, starting from the early 1960s.



**Figure 2.** Projected power densities for highfrequency  $ac + dc$  filter capacitors.

The development of new solid and liquid materials, in con- $\theta$  than tenth-scale in unit capacitance (4–9). junction with advanced methods of manufacturing technol- An example of the projected increase in energy density of ther is a tightly integrated material/component set of devel- of Figure 2 (2,8,13–15). Achieving the power densities, at, opment programs tailored to areas of need for the main say, an operational frequency of 10 kHz, of between 10 MVAR

est ( $\geq 1$  MHz) can cost-effective designs of such power systems classes of capacitor technology (7,18–21). The advancement of be practical for both the international marketplace and do- capacitor technology to date has been successful because of mestic use (7,14,15). Ceramics presently appear to be one the preeminent role that capacitor developers in industry intrinsically high-temperature, and hence long-lived, technol- have directly taken in integrating materials development into ogy available with a very large potential for advancement, the practical realization of advanced capacitors (7,18,19,21). particularly with the recent advent of new materials and the The power source developers of the future may well find that multilayer ceramic capacitor's (MLC) demonstrated produc- working together in this materials technology arena will ention capacitance and voltage scalability  $\gg 100 \mu$ F,  $> 500$  able a systems-responsive technology development program WVdc (11). Costs are also coming down from \$1 per micro- in each of the major capacitor technology areas. This would farad a few years ago, to less that \$0.25 per microfarad to- result in demonstration subscale hardware that will operate day (11). **at the power and energy densities needed, being no smaller** 

ogy, is feasible with tools emerging from present successful electrostatic and electrochemical capacitors for use in technology programs (6–9,18,19). What will be required fur- switched-mode power supplies is illustrated in the trend plot

**Table 4. Summary of Capacitor Characteristics***<sup>a</sup>*

Table +. Dummary or Capacitor Unaracteristics						
Ceramic	Electrolytic	Film				
Commercially available sizes:						
10 pF-100 $\mu$ F	$0.1 - 2,000,000 \mu F$	100 pF-5,000 $\mu$ F				
Operating voltage:						
$(Vdc)$ 25-500	$6 - 600$	25-300,000				
(Vac) $25 - 500$	$110 - 330b$	$25 - 5,000$				
Dissipation factor $(\%)$ :						
$1$ kHz: 0.15–2.5	$2 - 10$	$0.05 - 1.5$				
100 kHz: $<$ 1		$< 0.1 - 10$				
Gravimetric energy density:						
$0.005 - 0.50$ (kJ/kg)	$0.05 - 0.7$	$0.1 - 2.5$				
General relative cost:						
$1\times$	$3\times$	$1\times -10\times$				
		(size dependent)				

*<sup>a</sup>* Presently available capacitor performance parameter ranges available in the commercial marketplace. *<sup>b</sup>* Short-term ac duty.



ergy transfer time, ranging from microseconds through thousands of

and 20 MVAR per cubic meter would mean a reduced capaci-<br>tor volume fraction in such systems from the 30% to 50% of for the output. All capacitors must be surface mount com-<br>today to negligible proportions (<5%) in the ne 8). The inductance and internal series loss resistances at the higher frequencies of operation will also be reduced propor- **Inverter and ac Motor Drives.** Now operating above 20 kHz, tionately to achieve higher frequency operation at higher ef- inverters and ac motor drives require low-loss, pulse-decouficiencies (4–9,19–21). Clearly, the new chemical double layer pling (snubbing) and high-current dc link/bypass capacitors. technology whose performance is illustrated in Fig. 3 will Film capacitors are used for the IGBT decoupling and bypass evolve to fill the important technology performance position whereas banks of aluminum electrolytic capacitors are used between the capabilities of modern batteries and conventional on the dc link bus. Surface mounting is not presently much of capacitors. Rapid progress in this area is expected, and new an issue, but component selection is becoming more critical product lines are under development.  $\qquad \qquad$  as the switching frequency increases.

In the following status update section on film (Ian Clelland

Modern high-frequency switching converters designed around The MLP capacitor, best described as a construction hybrid MOSFET technology have attained new, higher levels of re- between MLC and stacked, plastic film capacitors is fully surliability due to quality improvements made in switching di- face mount compatible. The parts were developed for highodes and the employment of zero-transition switching. This frequency, ripple-current handling and high-pulse applicais less true for inverters using hard-switched integrated gate tions demanding over 10 years of operating life. The chip and bipolar transistors (IGBT) diode sets, but the power switch block shaped parts are not subject to the aging, cracking, and quality trend is still positive. An increase in switching fre- shorting sometimes experienced in other capacitor systems. quency has allowed significant size reduction of the magnetic The system substitutes the catastrophic single point of failure and reactive filter components, but this has also shifted the (shorting and heating) with a more gentle failure mode.

circuit's critical stress point. More attention must now be paid to the filter components and in particular to the filter capacitors that must operate at very high ripple and load currents relative to their small size. Like any electrical/electronic component, all capacitor technologies have potential wear-out and failure mechanisms which depend on voltage, frequency, temperature, and time. When dramatically increasing any one of these parameters (such as the frequency), much more care must be taken in choosing the proper component for the application. Because of their proven reliability and endurance, plastic film capacitors have historically been specified for critical applications. Evolved from plastic film technology, a novel *multilayer polymer* (MLP) technology utilizing metallized polymer film laminated into high density stacks is now contributing to power system reliability because of its stability under operating stresses and its inherently low impedance per unit volume.

### **Trends and Solutions**

Figure 3. Capabilities of batteries, electrochemical capacitors, and<br>electrostatic capacitors as functions of energy and power densities.<br>Each nower source optimizes over specific parametric regions of engineerators due to Each power source optimizes over specific parametric regions of en-<br>ergy transfer time, ranging from microseconds through thousands of ated harmonics. The input and resonant power train sections seconds. Appropriate efficiency energy transfer time technologies can need low-loss capacitors to achieve low impedance at high frebe readily identified (1,23,28). quency. The output filter sections require large capacitance values for load current holdup and low voltage ripple current handling. Ceramic or film capacitors are used in the input

and R. Price), tantalum (John Prymak), ceramic (John Pry-<br>
mak), electrolytic (Martin Hudis), mica (John Bowers), and<br>
related technologies, progress over the last few years and<br>
projections of the future will be addressed large and unsuitable for surface mounting, so an evolution is **ULTRALOW ESR MULTILAYER POLYMER CAPACITORS** taking place at the component level. To achieve significant **PROVIDE STABILITY AND RELIABILITY IN POWER** size reduction and produce a low profile input module, MLP **PROVIDE STABILITY AND RELIABILITY IN POWER** size reduction and produce a low profile input module, MLP<br> **CONVERSION APPLICATIONS** capacitors are proposed for the EMI filter section. capacitors are proposed for the EMI filter section.

### **Background Polymer Dielectric Approach**



itors covers the range from 0.047  $\mu$ F through 20  $\mu$ F with volt- ducing the size of resonant power converters. ages from 25 Vdc to 500 Vdc. Today, this technology is leading in *CV* density and is growing most rapidly in input voltage **High-Frequency Power Conversion Applications** filtering from 48 V to 400 V and output filtering at 24 V to 48 V. Many of the products are available in surface mount High-frequency dc to dc converters require a wideband input styles as lead-framed construction or as true *chip* capacitors. filter and sufficient output capacitance to drive the load dur-A key element in the success of this system is the gentle fail- ing the off-duty cycle. Because of wide use in telecommunicaure mode, which manifests itself as a gradual loss of capaci- tion systems, 48 V dc bus (plus an ac component) filtering is tance. Because the units can self-clear, short-circuiting as the approached with a 100 V rated electrostatic capacitor. Offsingle point of failure is virtually eliminated. The body of the line, computer, and aviation bus voltages range from 300 V to units is *plastic* eliminating the well-known problem of crack- 370 V and require a 400 V input capacitor. The capacitor ing caused by temperature coefficient of expansion (TCE). must act as a low-pass filter to the input ripple voltage, which

ene napthalate (PEN) and polyphenylene sulfide (PPS). The dielectric selected is based on the specific environmental and electrical properties required. PET and PEN are voltage-stable materials that compete favorably with X7R ceramic capacitor types. PPS is a very low loss and temperature-stable dielectric which offers size reduction compared to zero temperature coefficient ceramic chips.

PET thin-film dielectric has been available at 1.5  $\mu$ m thickness for over 10 years. This material is now commercially available from multiple sources down to  $1.2 \mu m$  and  $0.9 \mu m$  $\mu$ m thickness (with 0.6  $\mu$ m in development) that is allowing another expansion of MLP capacitor capacitance-voltage products. PET was selected because of its good electrical characteristics, excellent reliability, and ready availability. PEN dielectric is now available down to 1.5  $\mu$ m and 1.35  $\mu$ m thickness. PEN film, a virtual clone of PET, has increased thermal resistance for surface mount applications and very good high-**Figure 4.** Examples of the newest surface mount MLP capacitors temperature electrical stability. Capacitor grade PPS film<br>designed for low-profile board mounting. was introduced several years ago to address the needs of surface mount technology and thermal resistance. PPS is an extremely low loss dielectric, similar to polypropylene and zero The present offering of nonpolar, highly stable MLP capac- temperature coefficient ceramics, which is contributing to re-

The photo in Fig. 4 shows examples of the newest surface can be low frequency, and sees the reflected RFI due to the mount multilayer polymer capacitors designed for low-profile downstream switching noise. The capacitor typically selected board mounting. Lead frame pin-outs are offered at 0.100 in. is a MLP capstick capacitor (or alternately a ceramic type) (0.254 cm) pitch. Figure 5 shows a cross section of the capaci- with multiple leads for high current handling. Because of the tor section that highlights similarities to conventional met- frequency extremes and high voltage, the stability of PET is allized film and MLC constructions. The dielectric systems in desirable for good ripple attenuation and noise suppression. current use are polyethylene terephthalate (PET), polyethyl- The ESR of these filter capacitors is below 10 m $\Omega$  above 100



**Figure 5.** Cross section of the MLP capacitor body that highlights similarities to conventional metallized film and multilayer ceramic capacitor constructions.

kHz (see Fig. 6) allowing them to sink high ripple current. For output filtering these capacitor types are preferred over tantalum capacitors, especially at higher bus voltages, such as 48 V output.

Resonant and quasiresonant dc to dc converters achieve the highest power densities with good efficiency. For low voltage output, the circulating current in the resonant tank can be very high. For this application a 0.10  $\mu$ F to 0.22  $\mu$ F capacitor constructed with PPS is ideal. Polypropylene Film and COG ceramics work in this application but they are large and can be expensive. The capacitor can see in excess of 10 A rms at the switching frequency which makes the low dielectric loss of PPS highly desirable. These 5.0 mm lead-spacing PPS<br>capacitors in leading and surface mount packages are rated<br>voltage snubber and bypass applications. from 25 Vdc to 400 Vdc for various output voltages.

### **Inverter Bus Applications**

higher IGBT switching. The snubber and bypass capacitors are physically large and inductive at present. New MLP highvoltage chip capacitors are proposed for greatly reducing the **Introduction** size and height profile of the inverter package. The automo-<br>tive industry is driving this effort because of the electric vehi-<br>cle and various charging system requirements. The illustra-<br>tion in Figure 7 shows the propose

Power conversion applications still require large capacitors to tors, high-peak-current capacitors, and high-frequency capac-<br>carry high load currents, and these are generally electrolytic itors. Liquid metallized film cap carry high load currents, and these are generally electrolytic itors. Liquid metallized film capacitors are available in many<br>in nature (aluminum or tantalum types). Because of the poor different constructions *Liquid fill* in nature (aluminum or tantalum types). Because of the poor different constructions. *Liquid filled* refers to a wound section



erally less than 10 m $\Omega$  above 100 kHz, supporting sinking high rms

IGBT snubber size comparison



## Space and efficiency constraints have forced 20 kHz and **TECHNOLOGICAL EVOLUTION IN METALLIZED POLYMERIC**<br>higher IGBT switching The snubber and bynass canacitors **FILM CAPACITORS OVER THE PAST 10 YEARS**

Metallized film technology has evolved into dry and liquid<br>ac line-frequency capacitors, low- and high-voltage dc capaci-<br>Power conversion applications still require large capacitors to the high-peak-current capacitors, an frequency response of electrolytic types above 100 kHz, electioned in a liquid dielectric fluid. The dielectric fluid trostatic capacitors are filling more of the filter capacitor does not penetrate between the metallized impregnated construction comes from the use of hazy dielectric film. Hazy film contains an embossed surface (typically 6% to 12% space factor) allowing the dielectric fluid to penetrate between the film layers. Dry film capacitors are available using either metallized film or film foil, but this paper is confined to liquid-filled and dry metallized technologies (i.e., no foil construction). Ac line-frequency, high-frequency and high-peak-current capacitors all use polypropylene (PP) film because they require a low dissipation factor typically less than 0.1%. Dc-rated capacitors tend to use polyester (PET) because they require very thin gauges and a large modulus of elasticity for machine winding. In addition, the dc applications do not require a very small dissipation factor like ac capacitors and can generally use 1% limit.

Design evolution occurred slowly from 1960 to 1985, resulting today in an image as a mature industry, that is, very little change took place after 1985. During that 25-year period Figure 6. The ESR of 400 V class MLP capacitors used for power<br>supply output filters for good ripple attenuation and noise suppres-<br>sion up into the multimegahertz frequency regime. The ESRs are gen-<br>erally less than 10 mQ ripple currents  $\geq 15$  A<sub>rm</sub>.





**Figure 8.** Example of (top) the metal case liquid-filled and (bottom) plastic case dry-potted motor run capacitor.

status with many changes occurring over the last decade. Following are specific examples of these developments:

- 1. Liquid-filled, self-protected motor run capacitors progressing from metal case to plastic case
- 2. Self-protected motor run capacitors with a pressure interrupter progressing from a liquid-filled metal case to a dry-potted plastic case including the introduction of segmented metallized electrodes
- 3. Pitch-potted fluorescent ballast capacitors  $(\leq 660 \text{ Vac})$ going from a liquid-impregnated metal case to drycoated construction using wax blends for the coating
- 4. High-voltage rate-of-rise snubbers progressing from a liquid-impregnated metal case to a dry-potted plastic **Figure 9.** Examples of segmented, metallized electrode patterns.

case, including, in some cases, the transition from foil construction to metallized electrode construction

- 5. High-frequency ac capacitors progressing from foil liquid-impregnated construction to metallized dry construction
- 6. Very high peak power energy-discharge capacitors progressing from foil/paper construction to metallized kraft/ film construction.

### **Discussion of Examples**

**Self-Protected Motor Run Capacitors.** Line-frequency motor run capacitors require both long service life and fault protection. Over the years, this required a liquid-filled metal case capacitor incorporating a pressure interrupter. By 1985, this technology began to be replaced above the 200 Vac level with a plastic case, liquid-filled capacitor incorporating a pressure interrupter molded into the cover, and below the 440 Vac level with dry-potted, segmented metallized film construction. An example of the plastic case, liquid-filled capacitor is shown in Fig. 8 (top), and an example of the dry-potted, segmented metallized capacitor is shown in Fig. 8 (bottom).

The plastic case, liquid-filled capacitor utilizes an ultrasonic weld for the cover-case seam that is both leak tight and can withstand the high internal gas pressure which develops during a fault interruption of the pressure interrupter. Examples of segmented metallized electrode patterns are shown in Fig. 9. In general the continuous metallized pattern is divided up into segments connected to the end spray (schooping) through fusible links. The fusible links isolate the individual faulted segments giving rise to a soft failure mode, that is, capacitors fail open not short. In the dry-potted, segmented metallized film construction, the segmented pattern provides the equivalent function to the pressure interrupter. The common and attractive attributes for both new constructions are the plastic case and completely automatic assembly. The plas-



tic case, unlike the metal case, does not rust, does not dent, had a measurable impact. The changes in a couple of the reand does not require grounding. Completely automatic assem- ally significant technologies are briefly discussed in the folbly leads to a lower workmanship defect level which results lowing: in a higher mean time between failures (MTBF).

High-Current Snubbers. High-peak-current and high  $dV/dt$  Vac), liquid encapsulation is required to achieve long-term<br>film capacitors have also been available for many years, but Vac), liquid encapsulation is required to a

Large energy discharge capacitors are commonly used for laser fusion, magnetic forming, electromagnetic guns, defibril- **Polymeric Packaging and Encapsulation.** Injection molding lators, large strobe lights, to name a few examples. These ca-<br>pacitors can be as large as 125 kJ. Stored energy density for ease and cover with a built-in pressure interrupter. These pacitors can be as large as 125 kJ. Stored energy density for case and cover with a built-in pressure interrupter. These<br>energy discharge (EDC) has increased from less than 0.3 cases and covers are leak-tight and can withs energy discharge (EDC) has increased from less than  $0.3$  cases and covers are leak-tight and can withstand high fault  $J/cm<sup>3</sup>$  to over 1.5  $J/cm<sup>3</sup>$  during the past 10-year period. This pressure These new chemistrie  $J/cm<sup>3</sup>$  to over 1.5  $J/cm<sup>3</sup>$  during the past 10-year period. This pressure. These new chemistries provide superior humidity technology has been accomplished by moving from foil with resistance improved dielectric s technology has been accomplished by moving from foil with resistance, improved dielectric strength and can be applied<br>kraft paper construction to metallized kraft paper with poly- with a much faster process which translate mer film construction. Energy density is only one of the capac-

allized film capacitor performance. Some of these have lurgy has changed from aluminum to zinc to a new generation changed over the past 10 years, and others have not. These of alloy. Zinc has a lower clearing energy than aluminum but

- 1. Unmetallized polymer film dielectric strength
- 
- 
- 
- 
- 

**Dielectric Fluids.** For higher voltage ac applications  $(\geq 370)$ 

voltage can be traced to advancements in both the dielectric **High-Pulse Power Energy Discharge fluids** and the metallization.

with a much faster process which translates into lower cost.

itor's performance parameters which has improved during<br>this 10 year period. Voltage-reversal-withstand capability,<br>peak-current capability, and cycle aging under various condi-<br>tions have all improved dramatically with t W/cm<sup>2</sup> for ac applications. The clearing energy is directly re-<br>ated to the thickness of the metallization layer which in turn **Technologies.** Six technologies play a major role in met- affects the electric stress which can be applied. The metaltechnologies are the following: does not have the same corrosion resistance to humidity. The newest generation of alloys has both a low clearing energy

2. High temperature polymers for dielectric films<br>3. Dielectric fluids and capacitor processing<br>4. Lead attachment processing<br>5. Polymeric packaging and encapsulation<br>5. Polymeric packaging and encapsulation<br>5. Polymeric p has been the metallization of segmented patterns with high-6. Metallurgy and metallization patterns. speed manufacturing processes. Dielectric film coatings, used either as a substrate for the metallization layer or a protected Of these six technologies, unmetallized PP and PET poly- coating on top of the metallization layer, have also been used mer film dielectric strengths have had very little impact on during the past 10 years. Although this is not a metallizing the metallized film capacitor changes which have taken place technology, coated dielectric film can interact with the met-<br>over the past 10 years. The other five technologies have all allized layer during the humidity corr allized layer during the humidity corrosion process and/or

mance. (22). Capacitor-grade mica paper does not contain binders, ad-

The combination of metallized alloys, high surface resistance<br>
(thinner metallized layers), dielectric film coatings, and seg-<br>
mented patterns has contributed in large part to the changes<br>
in film capacitor-grade, recons

# **TEMPERATURE POWER ELECTRONICS APPLICATIONS** sions can be achieved.

signed for commercial, aerospace, and military applications outstanding electrical, environmental, and physical characrequire highly reliable components. These types of power elec- teristics (4,24). Most notably, these parts exhibit long life, a tronics circuits and systems include, or can include, the use very low capacitance drift over the entire temperature range, of reconstituted mica paper capacitors. Reconstituted mica withstand high voltages, are naturally resistant to the effects paper capacitors are particularly suited for operation where of partial discharges, and exhibit low radiation-induced conhigh ambient temperatures exist (18) and are an excellent ductivity caused by the absorption of ionizing radiation, such choice for these types of systems. as x-rays, gamma rays, and neutrons. In addition, they ex-

Reconstituted mica paper capacitors are typically used for en-<br>ergy storage, filtering, coupling, etc., in high-voltage, high-<br>temperature applications where radiation resistance, corona<br>resistance (in megaohms times micr capacitance stability (with respect to temperature, voltage **Reliability** frequency, or mechanical stresses) are required. These types of applications include, but are not limited to the following: High reliability is the greatest strength of reconstituted mica

- 
- ECM power supplies
- High-voltage transmitters for missile applications
- High-voltage TWT power supplies
- Ignition systems
- Power transmission systems
- Laser devices
- Gas and oil exploration equipment.

Small, high-voltage electronic modules can be designed and manufactured to include these types of capacitors in conjunction with other high-voltage components (i.e., resistors, diodes, spark gaps, strip lines, inductors).

### **Design and Construction**

The dielectric material used in designing and constructing these types of capacitors is reconstituted mica paper impregnated with a liquid polymer resin (i.e., polyester, epoxy, or silicone). The National Electrical Manufacturers Association defines mica paper as flexible, continuous, and uniform layers of mica reconstituted into a paperlike, electrical insulating **Figure 10.** Typical reconstituted mica capacitor change in capacimaterial composed entirely of small, thin, overlapping flakes or platelets with sufficient strength to be self-supporting and tion resistance (in M $\Omega \times \mu$ F) from -55° to 125°C.

during the clearing process resulting in improved perfor- to be capable of being wound into roll form for commercial use hesives, foreign matter, or coloring agents and is substan-**Conclusions** tially free of any substance which will adversely affect its per-

tuted mica paper ranges in thickness from 12.7  $\mu$ m (0.0005) **CHARACTERIZATION OF RECONSTITUTED MICA PAPER** in.) to 50.8  $\mu$ m (0.002 in. Depending on the type of packaging, **CAPACITORS USED IN HIGH-VOLTAGE AND HIGH-** capacitance, voltage rating, terminations, etc., various dimen-

### **Introduction Electrical, Environmental, and Physical Characteristics**

High-voltage, high-temperature power electronics systems de- Reconstituted mica paper capacitors are well known for their hibit a fractional voltage or charge loss as a function of the **Applications** absorbed dose.

paper capacitors. A complete understanding of the customer's • Airborne or surface radar systems requirements, proper design, the selection of highly reliable





tance, dissipation factor (i.e.,  $ac + pulse$  power losses), and dc insula-

materials, and tight control of the manufacturing and testing processes all lead to the reputation of these types of capacitors.

Studies are currently being conducted to determine the voltage and temperature acceleration factors for the dc life of reconstituted mica paper capacitors. A voltage acceleration factor of 7 to 10 is typically used for reconstituted capacitors.

Standard electrical tests (i.e., capacitance, dissipation factor, and dielectric withstand) are completed for every capacitor. Other electrical tests normally conducted on a sampling basis include insulation resistance, ac and dc partial discharge, burn-in, pulse discharge, and inductance.

Environmental tests are frequently conducted in accordance with customer and/or military specifications. For example, these tests include temperature shock, barometric pressure, humidity resistance, extreme temperature, and so on. Sure, numary resistance, extreme temperature, and so on.<br>Typical physical tests include shock, vibration, solderability, resistance to soldering heat, resistance to solvents, and terminal strength. **Figure 11.** A typical ceramic capacitor construction in cross section

The applications, design and construction, electrical, environmental, and physical characteristics, and reliability of this type of capacitor have been described. High-reliability recon- meric film, and the film carries the ceramic deposit through stituted mica paper capacitors provide outstanding character- the process. After the metal plate patterns are screened on istics when properly designed, manufactured, tested, and ap- the ceramic layer, the ceramic layer is lifted off the polymer plied to high-voltage and high-temperature power electronics carrier and placed into a stacking die for compression and systems. And the systems of the systems of the systems of the systems. And the systems of the systems

ments of ferroelectric ceramics in the late 1940s and 1950s cess and led the push to thinner dielectric thickness. led to the greatest growth spurt for this type of capacitor. The The most recent developments for ceramic capacitors have

$$
C = \kappa \epsilon_0 (A/t) \% (n-1)
$$

the ceramic layers are built up. The *tape* or *dry* method in- board can also apply enough stress to the chip to cause volves casting the ceramic slurry and plastic binders into a cracks, and the larger the chip, the greater the susceptibility dry tape. The tape thickness is controlled by process and ma- to either of these damages. Chips larger than these require a terial parameters. This method usually involved handling un- lead-frame attachment that relieves the flexural and thermal supported ceramic *sheets*, but now processing is on a poly- expansion stresses.



for a completed part. Material issues for performance enhancement are described in (1). **Conclusions**

The *wet* method requires that the ceramic slurry be deposited by squeegee on a base plate, usually glass. Then the de-<br>posited layer is dried after each layer is deposited. The metal electrode pattern is also applied wet, and after each applica- **Introduction** tion of the patterns, they must also be dried. This method Ceramic capacitors have been in use since the 1940s. Develop- came before the film carrier was introduced to the *tape* pro-

 $BaTiO<sub>3</sub>$  ceramics are used almost extensively in these capaci- improved volumetric efficiency thereby increasing the capacitors through to the present, with recent challenges by the lat- tance range available with these devices. Looking back at the est developments in Pb $(Zr, Ti)O_3$  and other Pb-based ce- formula for capacitance, the factors that can be manipulated ramics. to increase capacitance involve the *k* or dielectric constant, The main construction employed today is the multilayer the area, and the thickness. The area is somewhat restricted chip capacitor. These chips are still being offered with radial if these devices are to remain monolithic surface mount packand axial leads attached, but this is a dying business and the ages. Ceramic capacitors are susceptible to thermal and mesurface mountable chips dominate the market. As this con-<br>struction involves multiple layers (Fig. 11), the formula for subsequent stress transfer from the boards themselves. These struction involves multiple layers (Fig. 11), the formula for subsequent stress transfer from the boards themselves. These capacitance C based on the physical parameters of the ce-<br>ceramic materials are brittle and have n capacitance *C* based on the physical parameters of the ce-<br>ramic materials are brittle and have poor thermal transfer<br>capacitor is as follows:<br>capabilities. As such they develop thermal gradients large capabilities. As such, they develop thermal gradients large enough to crack them if they are heated too rapidly or if their mass is significant, as in very large chips. Chip sizes up to 3.8 where  $\epsilon_0$  is the permittivity of free space;  $\kappa$  is the relative per-<br>mittivity multiplier (hereafter referred to as the dielectric<br>constant); A is the area; and t is the thickness.<br>constant) and t is the thickness. expansion dissimilar to that of the ceramic. This difference in **State of the Art and Characteristics** thermal expansion defines the maximum chip size to be The two methods of assembly for this capacitor vary in how mounted directly to the board. Flexural movement of the



Figure 12. Ceramic capacitor variation in actual capacitance as a<br>result in the change in the relative dielectric constant  $K$  as a function<br>of temperature for several standard classes of capacitors.<br>When ceramic capacito

constant ceramics usually have higher temperature and volt-

package size is fixed, twice the number of layers of the half halving the dielectric thickness increases capacitance by a tance to achieve full-load ripple reduction similar to that of factor of four. This is where the largest gains have been made the ceramic capacitor filters. factor of four. This is where the largest gains have been made to date. The thinnest ceramic dielectric previously produced had a 50 WVdc (12  $\mu$ m thickness) rating which has been reduced to 25, 16, 10, and in rare cases, 6 WVdc (down to 2  $\mu$ m to 3  $\mu$ m thickness).

**Ceramic Capacitors for Small-Signal Applications.** The growth of ceramic capacitors has been mainly in small signal applications and only recently in power applications. Their small size, performance, cost and availability have led them to dominate small-signal processing from filtering to decoupling. It has really been the decoupling of IC circuitry that has allowed the ceramic market to develop along with the growth of the semiconductor industry. This application is well suited for a device that excels in high frequency and transient performance, is low cost, and is available in a surface mount package.



**Figure 13.** Ceramic capacitor voltage coefficient for high dielectric **Figure 14.** Frequency response comparison among aluminum, ceconstant formulations. The constant formulations constant formulations.

**Ceramic Capacitors in Power Applications.** The growth of ceramic capacitors in switched-mode power supply (SMPS) applications is directly tied to the increased frequency designs in these systems. As the frequency increases, the magnitude of the capacitance required decreases along with the decreasing inductance of the choke. These decreases are the primary reasons for the increased frequencies as smaller element requirements translate into smaller component sizes. The real goal is the smaller sized components for smaller package sizes of the SMPS itself. Also, the capacitances used in many power supply designs are overkill brought about by the need for lower ESRs (the ESR of a family of capacitors is usually in-

ceramic type is two to three orders of magnitude lower in The dielectric constant  $(k)$  can be manipulated to increase ESR. This lower ESR allows a window where the impedance pacitance but at a cost of temperature  $(Fig. 12)$  and bias is also dramatically lower  $(Fig. 14)$ . The ceram capacitance but at a cost of temperature (Fig. 12) and bias is also dramatically lower (Fig. 14). The ceramic capacitor re-<br>stability (Fig. 13) of the capacitance. The higher dielectric sponds nearly like a true RLC circu stability (Fig. 13) of the capacitance. The higher dielectric sponds nearly like a true *RLC* circuit with little capacitance age sensitivity in capacitance.<br>Roth the area and the dielectric constant manipulation of ferent types, but because the electrolytics have dramatically Both the area and the dielectric constant manipulation of-<br>caliform types, but because the electrolytics have dramatically<br>i.e. a direct relationship with capacitance. Doubling either decreasing capacitance, wish increasin fer a direct relationship with capacitance. Doubling either, decreasing capacitance, wish increasing frequency, the ESLs<br>doubles the capacitance, but the thickness offers a geometric are also significantly higher. In appli doubles the capacitance, but the thickness offers a geometric are also significantly higher. In application, because of their<br>gain. If the thickness of the dielectric is reduced by half, the lower ESR and insignificant cap gain. If the thickness of the dielectric is reduced by half, the lower ESR and insignificant capacitance roll-off in high fre-<br>capacitance per layer of the capacitor doubles. Because the quency, typical swapping of ceramic capacitance per layer of the capacitor doubles. Because the quency, typical swapping of ceramic for electrolytic types re-<br>nackage size is fixed, twice the number of layers of the half sults in ratios of capacitance from thickness dielectric can be built into the package. Therefore Electrolytics need to be some 8 to 20 times greater in capaci-



quencies, where the ESR decreases, because it continues al- ment of multiple, true surface mount chips is still cheaper most to mirror the decay in capacitive reactance. On the other than the more expensive leadframe devices. Improvements in hand, lower frequencies can activate a piezoelectric response volumetric efficiency through thinner dielectrics will greatly that may be detrimental to the ceramic chip and especially to enhance this solution. the multiple chip packages. At low frequencies  $< 500$  Hz, the ESRs of ceramic capacitors of value comparable to electrolytic **SOLID TANTALUM CAPACITORS** types are actually higher. Ceramic capacitors performed poorly in these early linear supply circuits and were shunned **Introduction** by design engineers for this application. In moving into the high-frequency realm, ceramic capacitors have become the The solid tantalum capacitor was originally developed by Bell<br>preferred device because of their low power losses and induc-<br>Telephone Laboratories. It evolved from t tances, leading to much smaller volume capacitors than elec- pacitor that used a porous anode block with the liquid electrotrolytics for comparable ripple reduction. lyte solution replaced by a semiconductor solid. Problems of

these capacitors to optimized performance with very low as- with this approach. Conventional hermetic sealing was now pect ratios (length divided by width). Aspect ratios down to possible with the elimination of the liquid electrolyte solution. 0.2 result in much lower ESR and ESL, and the extremely The construction of the tantalum capacitor utilizes a very short and wide thermal transfer path allows a much lower porous anode built with tantalum powder. The powder is temperature rise for equal amounts of power dissipation. Typ- pressed in a pellet form with a tantalum wire inserted (Fig. ical ESLs might be as low as 500 pH. Using a feedthrough 15). Then the pellet is sintered to allow contact growth among design (a four terminal MLC). ESLs as low as 100 pH are all individual particles (Fig. 16). The result achievable. that electrically connects all tantalum particles to each other

For the SMPS design from 100 kHz through 1 MHz, the and to the tantalum wire. ESR has made the MLC a preferred choice for performance. The dielectric is formed on the exposed surfaces of the tan-

silver in the electrode and convert to systems favoring nickel num electrolytics. or copper. The low-fire ceramics already use ratios of silver to The *counterelectrode* or cathode plate is formed by the elec-

leadframe. The equipment used in the manufacture of ceramic capacitors has always been optimized to produce smaller chip sizes, resulting in a performance sacrifice when manufacturing the larger sized units needed today. The chips themselves are built up in a mother pad configuration, stacking one layer at a time. For the smaller chip sizes, this mother pad may yield thousands of small chips, but only tens of the larger. This inefficiency is then multiplied if that pad is divided by five when a chip assembly requires five chips stacked in a leadframe. In addition, the test and handling equipment are not applicable to the manufacture of larger chip sizes. Their size and mass results in self-created physical damage when machine transported or fed in bulk. The smaller chips are light enough that their mass is far too small to cause damage to each other in bulk. The result for large chips is excessive hand labor and inefficient handling.

**Mounting Considerations.** Larger capacitances are now being made available in smaller surface mount chips. These chips may have to be spread out on the board to achieve even higher capacitance goals, but their performance is undeniably shared with the larger ceramics. Hand-in-hand with greater emphasis on distributed power supplies, their availability, **Figure 15.** Tantalum capacitor pellet construction at the pressing performance, cost, and process capability make them a pre- stage during fabrication.

The ceramic capacitor is more beneficial in the higher fre- ferred choice for future expansion into this market. Place-

Telephone Laboratories. It evolved from the *wet* tantalum ca-The MLC's ability to fit form to function allows designing sealing common to all electrolyte capacitors were eliminated

all individual particles (Fig. 16). The result is a porous block

Its low ESL will make it equally superior in the range of talum by electrochemical treatment which produces a  $Ta_2O_5$ SMPS designs above 1 MHz. (tantalum pentoxide) film (Fig. 17). This film is insulating and has a dielectric constant of approximately 22. Though this **Cost of Ceramics.** For the small surface-mountable com- constant is relatively small, the dielectric thicknesses are also mercial chips with capacitances up to a few microfarads, the extremely thin, and the surface area of the porous block is major cost factor is the metal, though these chips are already extremely high. The thickness is contr extremely high. The thickness is controlled by the process extremely inexpensive. The direction of the industry is to allowing different ratings for different bias applications. The eliminate the precious metals palladium, platinum, and even volumetric efficiency of this capacitor exceeds that of alumi-

palladium that have greatly lowered electrode costs. trolyte in the wet tantalums. This solution readily penetrates For the larger chips in these applications, the major cost the porous anode and forms itself to the exposed  $Ta_2O_5$  sur-<br>is the labor involved in handling, processing, and adding the faces. In the dry tantalum capacitor, faces. In the dry tantalum capacitor, the counterelectrode ma-





terial is  $MnO<sub>2</sub>$ , and it is formed in successive dip and dry pro- trolyte solution. cesses. As a solution, it penetrates the anode as a wet Their surface mount capability and large capacitance have with a coating of carbon and silver as the final coat (Fig. 18). provement over aluminum electrolytics.



nates the performance of this capacitor throughout the frequency spectrum. As a porous anode, the connections to the inner depths of the secondary electrode are through the same pores of the anode block. These paths are resistive and result in the appearance of an *RC* ladder effect with increasing frequency. The deepest penetration is through these channels or pores, and the resistance of this is cumulative.

With the higher frequencies, the resistance to the inner cells of capacitance makes the *RC* time constant of these elements greater than the period of the signal. This results in capacitance loss as they are effectively isolated from responding to the signal. Physically, the higher frequencies allow less penetration into the depths of the anode and depend more on the surface area of the anode block (Fig. 20). Electrically, the effect is a multiple *RC* ladder effect where the summary resistance to the inner capacitive cells and its capacitance cause the signal to have no effect on this element, electrically cutting them out of the circuit response.

**Figure 16.** Sintered tantalum capacitor pellet after high tempera- **Tantalum Capacitors for Small-Signal Applications.** The greatture processing. est growth in dry tantalum capacitors is in the surface mount version. These are plastic packaged devices that allow wave and reflow solder operations with no concerns for a *wet* elec-

electrolyte and upon drying leaves a film of  $MnO<sub>2</sub>$  behind, supplanted many aluminum electrolytic applications. Their which adheres to the exposed surfaces of the  $Ta_2O_5$ . This cath- temperature range eclipses that of the aluminum electrolytode plate is connected in the package to an external contact ics. Their frequency response in many cases is a decade im-

Applications include filtering, timing, power holdup, and **State of the Art and Characteristics** decoupling. Early assessments of this type in power applica-The tantalum capacitor has the highest volumetric efficiency<br>of any of the popular types of capacitors. The direction of de-<br>velopment in the industry has been to push that envelope fur-<br>velopment in the industry has been ments in process and material capabilities were always tied to improvements in volumetric efficiency, they may have been obscured in the push to reduce size. The extension of capacitor range and size reduction has always dictated the direction of tantalum chip improvements.

> **Tantalum Capacitors For Power Applications.** The power application of tantalum capacitors could not be effectively measured with the commercial product because the primary goal was always volumetric efficiency, with ESR always a secondary or sacrificial object. Power application required that the ESR be the primary goal and capacitance the dependent variable.

Working against the volumetric goals of the commercial chip with older powders that were larger and processes meant to obtain optimum penetration of thinner channels, the low ESR tantalum chip evolved. These devices were born out of customers' demands for this specific product. Their applica-Figure 17. Dielectric oxide formulation on exposed surfaces of a tan-<br>tion was for filtering, both input and output, of SMPS cirtalum capacitor. cuitry, never a standard application of tantalum capacitors.



lum capacitor package to an external contact via a coating of carbon and then silver as a final coat.

Their performance in this application may be decades worse not make any sense to build smaller case sizes with smaller than ceramics but they are readily surface mountable and capacitances, because capacitance is a secondary considerthey cost much less. They can easily withstand the surges and ation in this application. ESR is the primary concern. the constant ripple currents. These devices are all life tested and surge tested. They

traditional tantalum chip development philosophy. By using Vdc and back through millions of pulses with no failures. Exlarger powders, the surface area is reduced, but the channel tended ac current testing has shown that the heat buildup or pore size is increased. Using the same procedures used to within the part is proportional to the ESR, and because the fill the smaller pores, with some repetition because of larger ESR is so much lower, there is little additional heat develamounts of material to be deposited, the larger pores are oped internally. filled extremely densely. The result is a dramatic improve- Though dramatically improved, the ESR still contributes ment in ESR. A comparison of the two devices for common to an *RC* ladder effect. This limits the useful range of these

mercial products, specifically the *D* case and the *X* case. It did approach now.



Again, manufacturing moves in a direction opposite to the have been put on extended surge testing from 0 Vdc to rated

capacitances is shown in Fig. 21. capacitors to 500 kHz and below. The capacitance roll-off These devices are available in the largest sizes of the com- above this frequency leaves the ceramic as the only viable

> Tantalum capacitors require additional process steps and additional testing. There is a fairly small premium required to cover the additional costs. The resulting chips are packaged on reels with true surface mount capability. Surge and ripple capabilities not common with other commercial products allow power filtering and power decoupling applications with little cost incentives.

> The chips are packaged in reels and can be fed like any of the larger cased commercial surface mount products. Profiles for infrared reflow and wave solder procedures are the same as those for other commercial products.

### **Future Directions**

Lower ESR and higher capacitance are the goals in developing low ESR tantalum SMD capacitors. The graph in Fig. 22 shows the results of the work accomplished in making the tantalum capacitor more applicable in power or energy applications.

As shown in Fig. 22, the ESR limits for a 330  $\mu$ F, 6 WVdc Figure 19. Manufacturing steps in the fabrication of tantalum ca- rated X-Case (7342) chip vary dramatically as the product pacitors. type varies. T491 is the standard commercial chip with an

![](_page_15_Figure_1.jpeg)

**Figure 20.** Apparent *RC* ladder network equivalent circuit of the tantalum capacitor.

![](_page_15_Figure_3.jpeg)

**Figure 21.** Equivalent series resistance for low ESR and standard tantalum capacitors as a function of frequency.

![](_page_15_Figure_5.jpeg)

**Figure 22.** Equivalent series resistance decrease in the evolution of tantalum capacitor technology (KEMET $^{\mbox{\tiny{\rm TM}}}$ data)

but with greater restrictions on ESR, and its limit drops to Examples as specific rating extensions follow: 150 m $\Omega$ . The T494 incurs increased losses due to the tighter testing requirements plus additional testing not applied • Larger ripple current across the board to the T491. The T495 represents a true de- • Longer life expectancy parture from the standard product in test and limits (ESR • Larger energy density maximum of 100 m $\Omega$ ) and also in materials. Heat treatment • Lawer ESP (conjurators) maximum of 100 m $\Omega$ ) and also in materials. Heat treatment<br>experiments have allowed us to move the limits of the T495<br>lower still, to a specified limit of 65 m $\Omega$ . The MAT chip is a<br>design that employs a different geome

a higher resistive state such as  $Mn_2O_3$ . This conversion seals • Higher ambient temperature ratings ( $\geq 125^\circ$  to 200°C) or isolates the fault site in the capacitor. In actual manufaction is interesting ( $\geq 0.00 \text{$ or isolates the fault site in the capacitor. In actual manufacturing, there are many fault sites in the dielectric that cause<br>a conversion like this to take place and *heal* the capacitors<br>but it requires using the semico plate. It also requires restricting the current. If the fault site **New Products, Technology, and Specific Performance** is exposed to an unlimited current source, the conversion to a higher resistive state may not take place, resulting in a cata-<br>strophic failure.<br>be traced to increased foil gains (etched surface area per pro-

these fault sites, creating a loss of connection of the fault sites meter at a specific voltage). The improvement in the high-<br>in the dielectric in the same manner as the MnO<sub>2</sub>. The con-voltage anode foil gain over the pa ductive polymer offers two advantages over the  $MnO_2$ : it has Fig. 23 (25).<br>lower resistivity, and it does not offer a readily available Foil gain curves are a function of voltage and show the lower resistivity, and it does not offer a readily available source of oxygen on which tantalum feeds when the device same general improvement for low voltage typically in the fails catastrophically. 25 V to 75 V range as well as medium and high voltage. As

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EIA defined ESR limit of 500 m $\Omega$ . The T494 is the same chip quality are required today to be a major, worldwide supplier).

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anode structure, offering more surface area and requiring<br>lower depth penetration into the volume of the anode. This<br>allows the maximum limit now to drop to 30 mΩ.<br>The next offering will be the MAT chip with a conductive<br>

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strophic failure.<br>It has been shown that new polymer materials vaporize at iected surface area measured as microfarads per square centijected surface area measured as microfarads per square centivoltage anode foil gain over the past 10 years can be seen in

can be seen, in the 550 V to 600 V range (typical formation voltage for a 400 Vdc to 450 Vdc rated capacitor), the gains **ALUMINUM ELECTROLYTIC CAPACITORS** have increased by over a factor of two in ten years. Etching gains continue to come from improved control and uniformity **Market Direction** in the tunnel length, geometry, and spacing. The theoretical<br>imit on gain is still a long way from current performance, The aluminum electrolytic capacitor is a product which has<br>developed over many years and is still evolving at a rapid rate<br>today. The worldwide aluminum electrolytic capacitor indus-<br>try is over \$3 billion in sales and is

**Expected Life Performance.** Longer capacitor life can be • Motor drives **• Motor drives • Motor drives •** important items are the following: • Power supplies

- Uninterruptible **•** More stable aluminum oxide
- Switch-mode Smaller dc leakage currents
- Audio Improved self-healing (electrolyte chemistry)
- Appliance and small pump motors  $\bullet$  Improved  $H_2$  gas absorption (electrolyte chemistry)
	-
- Strobe and flash lamps Strobe and flash lamps Lower halogen contamination levels Decreased electrolyte leakage (deck to case sealing)
- Medical defibrillators Decreased electrolyte leakage (deck to case sealing) Medical defibrillators Smaller thermal resistance within the capacitor Electronic control circuits. Reduced dielectric stress  $(V/\mu m)$ 
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rating extensions (cost reduction and continuously improving chemistry, formation chemistry, capacitor construction, and

In general the evolution continues in size reduction and These developmental areas can be grouped in electrolyte

![](_page_17_Figure_1.jpeg)

Electrolytic capacitor specific anode foil gain versus formation voltage

**Figure 23.** High-voltage foil gain versus formation volt-**Figure 23.** High-voltage foll gain versus formation volt-<br>age from 1985 to 1995.

![](_page_17_Figure_6.jpeg)

microfarad as a function of the capacitance of the capacitor in micro-

capacitor design. The impact of these parameters on the rated The data in Fig. 24 summarize ripple current (120 Hz) perlife and the expected life performance can be seen through formance at name plate conditions offered today by many the catalog of changes over the past 10 years (26–28). Rated manufacturers (26–28). As a figure of merit, the ripple curlife has evolved from 1000 h and 2000 h to 3500 h and re- rent has been normalized to the size of the capacitor (surface cently to 5000 h (at name plate ratings) with expected life area is the key scaling parameter for ripple current, but vol-<br>going from 2000 h to values in the 12,000 h to 28,000 h range ume is a more convenient normalizing going from 2000 h to values in the 12,000 h to 28,000 h range ume is a more convenient normalizing parameter) for many<br>(the life expectancy is a function of the case diameter which capacitor ratings over a large selection (the life expectancy is a function of the case diameter which capacitor ratings over a large selection of snap-in and comin part accounts for the large spread in the expected life puter grade (screw terminal) products. Specifically this table range) (29). range) (29).<br>Larger specific ripple current ratings are being generated to 220 mm and temperature ratings at 85° and 105°C As can Larger specific ripple current ratings are being generated to 220 mm and temperature ratings at  $85^{\circ}$  and  $105^{\circ}$ C. As can<br>by reducing the ESR within the capacitor and reducing the bessen the data in the graph demons by reducing the ESR within the capacitor and reducing the be seen, the data in the graph demonstrates a dependence on thermal resistance from the section to the case and from the rated temperature rated voltage and the con thermal resistance from the section to the case and from the rated temperature, rated voltage, and the construction of the case to the mounting plate. The impact of this development cancertor Pitchless extended foil design case to the mounting plate. The impact of this development capacitor. Pitchless extended foil designs with thick case bot-<br>can be seen by the normalized data in Fig. 24. pacitors, whereas snap-in capacitors may use none or some of these techniques for improved heat transfer. Tracing the ripple current performance over a 10-year period would also show a dramatic change in the ripple current ratings. The data in Fig. 24 also show a high ripple current design (designated with an X) compared to the normal ripple current design and the impact on the ripple current rating by going from static cooling to active cooling. Increasing the ripple current ratings is a continual drive within the industry. Large electrolytic capacitors with over 50 A ripple current ratings are no longer difficult to obtain even when coupled with long life expectancy.

### **Product Availability and Further Development**

There are two major areas for new products. One is based on solid instead of liquid electrolytes specifically for higher voltage (30), and the second is hybrid design which uses different materials and/or geometries for the cathode and the anode (31). Both are under active development and have been discussed in the literature. The solid electrolyte has the potential for a much smaller capacitance and ESR temperature co-**Figure 24.** Specific ripple current measured as A<sub>rms</sub> (at 120 Hz) per efficient compared to the temperature coefficient for a liquid microfarad as a function of the capacitance of the capacitor in micro-electrolyte. Typi farads. with liquid electrolytes are in the 700 ppm range whereas the electrolyte resistivity can be two orders of magnitude<br>smaller for a solid electrolyte compared to a liquid electrolyte 12. J. Ennis, High energy capacitor development, Symp. High Power smaller for a solid electrolyte compared to a liquid electrolyte. 12. J. Ennis, High energy capacitor development, *Symp. High Power*<br>Electron, *Inst. State Univ. New York at Buffalo*. Buffalo. NY. No-Today solid electrolytes are available with ratings up to about<br>25 V, but the voltage should increase with time. The hybrid<br>25 V, but the voltage should increase with time. The hybrid<br>25 V, but the voltage should increase of which will limit the capacitor to slower frequency applications more typical of a battery than a capacitor, and to appli-<br>cations more typical of a battery than a capacitor, and to appli-<br>cations with reduced ripple cur already appearing which continue to cloud the dividing line Bulletin no. 13, 1987. between a capacitor and a battery. In addition to rating ex- 16. J. J. Svec, Capacitors from 0.01 ounce to 50 pounds, *Ceramic In*tension, these new technologies are providing the foundation *dustry,* pp. 32–34, August, 1979. for aluminum electrolytic capacitors with much longer life ex- 17. J. Hansen, Development of an 1100°F Capacitor, NASA, Wash-

A second trend within the industry is product proliferation. NASA-CR-1799, 1971.<br>Creased specific energy joules per cubic centimeter in- 18. W. J. Sarjeant, Capacitor fundamentals, *Proc. 1989 IEEE Electr*. Increased specific energy joules per cubic centimeter in- 18. W. J. Sarjeant, Capacitor fundamentals, *Proc.* creased rinnle current (amneres per microfared) and in- *Insulation Conf.*, Chicago, IL, 1989, pp. 1–51. *Insulation Conf.*, Chicago, IL, 1989, pp. 1–51.<br>creased life expectency usually are achieved individually but 19. The Department of Defense Critical Technologies Plan for the creased life expectancy usually are achieved individually but and the Department of Defense Critical Technologies Plan for the not collectively. The aluminum electrolytic capacitor is continumed to divide into multiple pro

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### **34 CAPACITOR STORAGE**

**CAPACITORS, THIN FILMS.** See THIN FILM CAPACITORS.